Applicant: Junichi NAKA, et al. Attorney's Docket No.: 28951.1175

Serial No.: 10/574,498 Filed: April 3, 2006

Page : 2 of 18

## Amendment to the Specification:

Prior to examination, please amend the specification as follows.

Page 20, replace lines 1-12, amended as follows:

--connected to a gate terminal of a MOS transistor from the detection target net list, and storing the extracted net in a extracted net database which is provided for each of MOS transistors having different threshold values; and a resistor insertion unit for inserting a resistor element having a <a href="https://district.org/high-resistance">high-resistance</a> value which does not affect the operations of circuits other than the extracted MOS transistor, between the extracted net that is connected to the gate terminal of the extracted MOS transistor and a power supply that is determined for each threshold value of the MOS transistor, and between the extracted net and a reference voltage, respectively, in the detection target net list, on the basis of the extracted net database that is provided for each of the MOS transistors having different threshold values.--

Page 33, replace lines 1-10, amended as follows:

--detection target net list, and storing the extracted not in an extracted net database which is provided for each of the MOS transistors having different threshold values; and a resistor insertion step of inserting a resistor element having a high resistance value which does not affect the operations of circuits other than the <a href="MOSTMOS">MOSTMOS</a> transistor or the sub-circuit, between the net extracted in the first net extraction step and the second net extraction step and a power supply, and between the extracted net and a reference voltage, respectively, in the detection target net list, on the basis of the extracted net database that is provided for each of the MOS transistors having different threshold values.--